

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

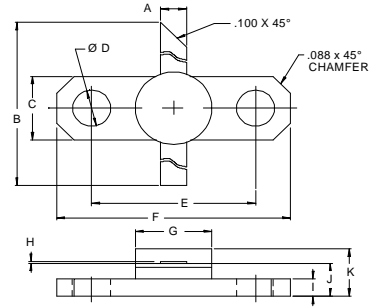
The **ASI AVF150** is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	11 A
<b>V<sub>CC</sub></b>	55 V
<b>P<sub>DISS</sub></b>	400 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +250 °C
<b>T<sub>STG</sub></b>	-65 °C to +200 °C
<b>θ<sub>JC</sub></b>	0.6 °C/W

**PACKAGE STYLE .250 2L FLG (B)**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	1.050 / 26.67	
C	.245 / 6.22	.255 / 6.48
D	.120 / 3.05	.140 / 3.56
E	.552 / 14.02	.572 / 14.53
F	.790 / 20.07	.810 / 20.57
G		.285 / 7.24
H	.003 / 0.08	.007 / 0.18
I	.052 / 1.32	.072 / 1.83
J	.120 / 3.05	.130 / 3.30
K		.210 / 5.33

**ORDER CODE: ASI10570**
**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 10 mA	65			<b>V</b>
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 15 mA      R <sub>BE</sub> = 10 Ω	65			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 1.0 mA	3.5			<b>V</b>
<b>I<sub>CES</sub></b>	V <sub>CE</sub> = 50 V			12.5	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 1.0 A	15		120	<b>---</b>
<b>P<sub>G</sub></b>	V <sub>CC</sub> = 43 V      P <sub>OUT</sub> = 150 W      f = 1030 - 1090	8.5			<b>dB</b>
<b>η<sub>C</sub></b>	MHZ	40			<b>%</b>